UTC UNISONIC TECHNOLOGIES CO., LTD

MJE13001

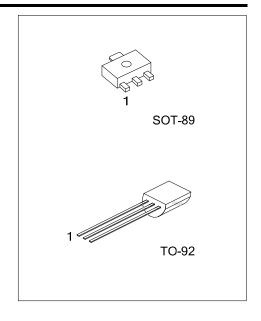
NPN SILICON TRANSISTOR

NPN SILICON POWER TRANSISTOR

FEATURES

* Collector-base voltage: V(BR)CBO=600V

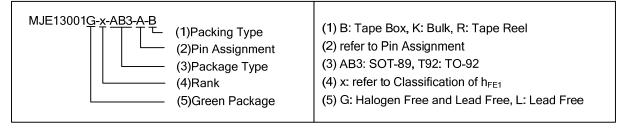
* Collector current: I_C=0.2A



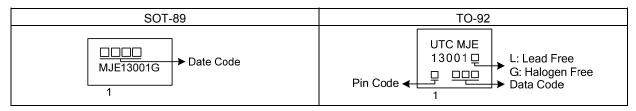
ORDERING INFORMATION

Ordering	Number		Pin	Assignm			
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	MJE13001G-x-AB3-A-R	SOT-89	Е	С	В	Tape Reel	
-	MJE13001G-x-AB3-F-R	SOT-89	В	С	Е	Tape Reel	
MJE13001L-x-T92-B	MJE13001G-x-T92-B	TO-92	В	С	Е	Tape Box	
MJE13001L-x-T92-K	MJE13001G-x-T92-K	TO-92	В	С	Е	Bulk	
MJE13001L-x-T92-A-B	MJE13001G-x-T92-A-B	TO-92	Е	С	В	Tape Box	
MJE13001L-x-T92-A-K	MJE13001G-x-T92-A-K	TO-92	E	С	В	Bulk	

Pin Assignment: C: Collector B: Base E: Emitter



MARKING



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V_{CEO}	400	V	
Collector-Base Voltage		V_{CBO}	600	V	
Emitter Base Voltage		V_{EBO}	7	V	
Collector Current		I _C	200	mA	
O-llastas Davida Disaination	SOT-89	-	550	\^/	
Collector Power Dissipation	TO-92	Pc	750	mW	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

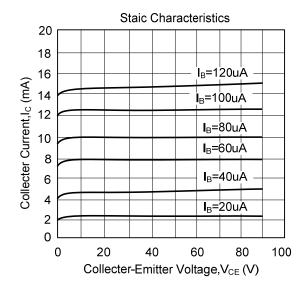
■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

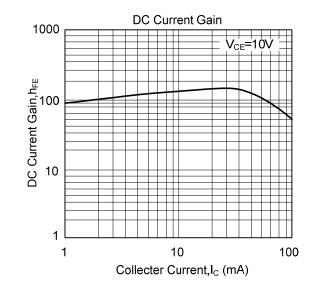
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT					
BV _{CBO}	I _C =100μA, I _E =0	600			V					
BV _{CEO}	I_C =1mA, I_B =0	400			V					
BV _{EBO}	I _E =100μA, I _C =0	7			V					
V_{BE}	I _E =100 mA			1.1	V					
I _{CBO}	V _{CB} =600V, I _E =0A			100	μΑ					
I _{CEO}	V _{CE} =400V, I _B =0			200	μΑ					
I _{EBO}	V _{EB} =7V, I _C =0A			100	μΑ					
ON CHARACTERISTICS										
h _{FE1} *	V _{CE} =20 V, I _C =20mA	10		70						
h _{FE2}	V _{CE} =10V, I _C =0.25mA	5								
V _{CE(SAT)}	I _C =50mA, I _B =10mA			0.5	V					
V _{BE(SAT)}	I _C =50mA, I _B =10mA			1.2	V					
SMALL-SIGNAL CHARACTERISTICS										
f⊤	I _C =20mA,V _{CE} =20V,f=1MHz	8			MHz					
Resistive Load										
ts	I _C =50mA, I _{B1} =-I _{B2} =5mA,			1.5	μs					
t _F	V _{CC} =45V			0.3	μs					
	BVCBO BVCEO BVEBO VBE ICBO ICEO IEBO hFE1* hFE2 VCE(SAT) VBE(SAT)	BVcBO	BVcBO	BV _{CBO} I _C =100μA, I _E =0	BVcBO					

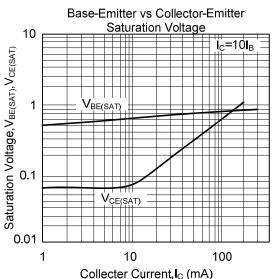
■ CLASSIFICATION OF h_{FE1}*

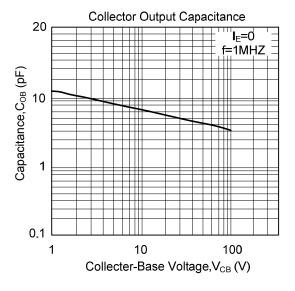
F	RANK	Α	В	С	D	Е	F	G	Η	I	J	K	L
R	ANGE	10-15	15-20	20-25	25-30	30-35	35-40	40-45	45-50	50-55	55-60	60-65	65-70

■ TYPICAL CHARACTERISTICS









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